

ABSTRACT**BONDING WIRE FOR SEMICONDUCTOR DEVICE**

There is provided a bonding wire for a semiconductor
5 device including a coating layer having Pd as a main
component on a surface of a Cu alloy core material and a
skin alloy layer containing Au and Pd on a surface of the
coating layer, the bonding wire further improving 2nd
bondability on a Pd-plated lead frame and achieving
10 excellent ball bondability even in a high-humidity heating
condition. The bonding wire for a semiconductor device
including the coating layer having Pd as a main component
on the surface of the Cu alloy core material and the skin
alloy layer containing Au and Pd on the surface of the
15 coating layer has a Cu concentration of 1 to 10 at% at an
outermost surface thereof and has the core material
containing either or both of Pd and Pt in a total amount of
0.1 to 3.0% by mass, thereby achieving improvement in the
2nd bondability and excellent ball bondability in the high-
20 humidity heating condition. Furthermore, a maximum
concentration of Au in the skin alloy layer is preferably
15 at% to 75 at%.